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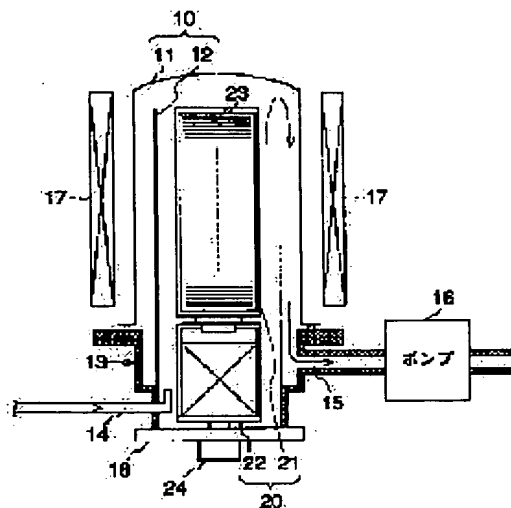
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(54) SEMICONDUCTOR WAFER SUPPORT BASE AND VAPOR GROWTH DEVICE

(57)Abstract:

PURPOSE: To provide a semiconductor wafer support base of a structure, wherein in the case where a B-containing amorphous Si film is deposited on semiconductor wafers at a comparatively low temperature and at a low pressure, the adhesive force of a film on the surfaces of components to be used is improve, the peeling of the film is made hard to cause and the wafer support base can be used without preventing the generation of dusts, and a vapor growth device using that semiconductor wafer support base.

CONSTITUTION: The respective surfaces of a wafer placement use boat 21, a heat insulating cylinder 22 for supporting the boat 21 and reaction outer and inner tubes 11 and 12 for housing these of the boat 21 and the cylinder 22 are subjected to sandblast treatment in such a way that the mean surface roughness Ra of the surfaces is 0.2 to $4\mu\text{m}$ and the mean interval Sm between the surface roughnesses of the surfaces is 20 to $1000\mu\text{m}$.



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